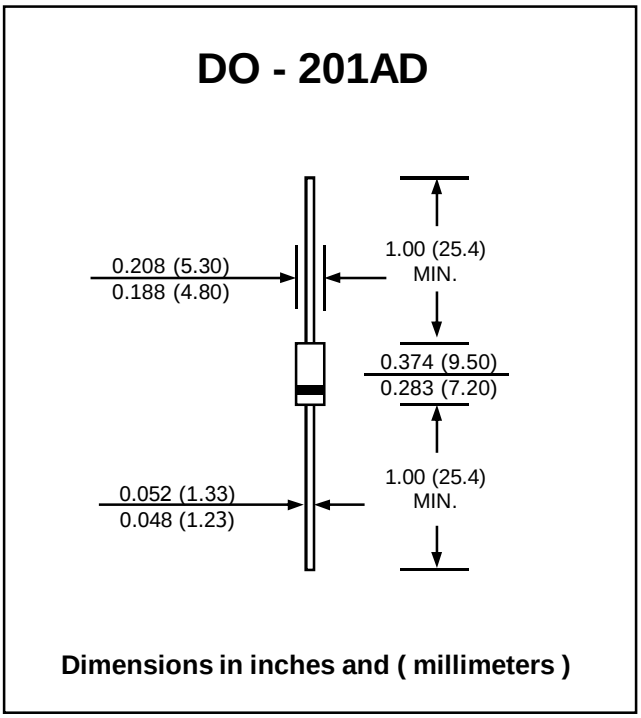
www.eicsemi.com

HVM12

SILICON RECTIFIER DIODE

PRV : 12000 Volts
Io : 350 mA



FEATURES :

* High current capability
* High surge current capability
* High reliability
* Low reverse current
* Low forward voltage drop
* Pb Free / RoHS Compliant

MECHANICAL DATA :

* Case : DO-201AD Molded plastic
* Epoxy : UL94V-0 rate flame retardant
* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
* Polarity : Color band denotes cathode end
* Mounting position : Any
* Weight : 0.929 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.

RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	12000	V
Maximum RMS Voltage	V_{RMS}	8400	V
Maximum DC Blocking Voltage	V_{DC}	12000	V
Maximum Average Forward Current, at Ta = 60 °C	I_F	350	mA
Peak Forward Surge Current, 8.3ms Single half sine wave Superimposed on rated load	I_{FSM}	30	A
Maximum Forward Voltage at I_F = 0.35 Amps.	V_F	12	V
Maximum DC Reverse Current Ta = 25 °C	I_R	10	µA
at rated DC Blocking Voltage Ta = 125 °C	$I_{R(H)}$	500	µA
Operating Junction Temperature	T_J	135	°C
Storage Temperature Range	T_{STG}	- 20 to + 135	°C

RATING AND CHARACTERISTIC CURVES (HVM12)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

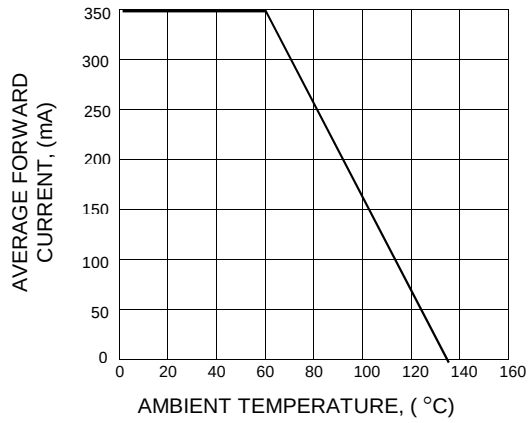


FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

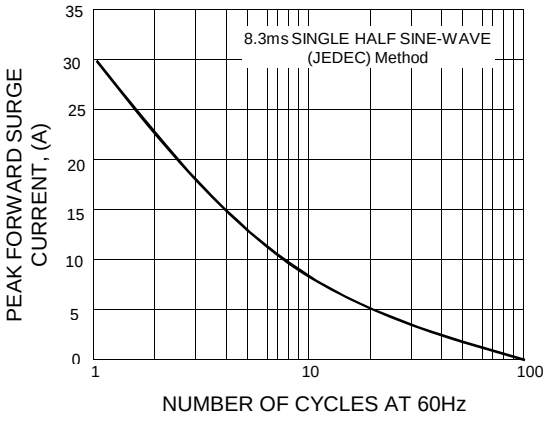


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

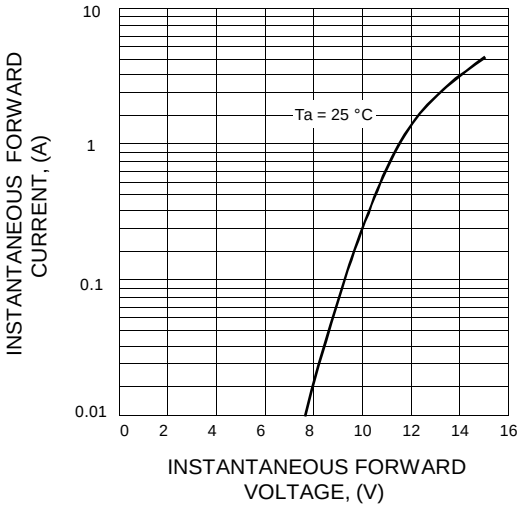


FIG.4 - TYPICAL REVERSE CHARACTERISTICS